

PROCEEDINGS OF SPIE

Low-Dimensional Materials and Devices 2016

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Editors

30–31 August 2016
San Diego, California, United States

Sponsored and Published by
SPIE

Volume 9924

Proceedings of SPIE 0277-786X, V. 9924

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Low-Dimensional Materials and Devices 2016, edited by Nobuhiko P. Kobayashi, A. Alec Talin, M. Saif Islam,
Albert V. Davydov, Proc. of SPIE Vol. 9924, 992401 · © 2016 SPIE · CCC code: 0277-786X/16/\$18
doi: 10.1117/12.2258072

Proc. of SPIE Vol. 9924 992401-1

The papers in this volume were part of the technical conference cited on the cover and title page. Papers were selected and subject to review by the editors and conference program committee. Some conference presentations may not be available for publication. Additional papers and presentation recordings may be available online in the SPIE Digital Library at SPIDigitalLibrary.org.

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Author(s), "Title of Paper," in *Low-Dimensional Materials and Devices 2016*, edited by Nobuhiko P. Kobayashi, A. Alec Talin, M. Saif Islam, Albert V. Davydov, Proceedings of SPIE Vol. 9924 (SPIE, Bellingham, WA, 2016) Six-digit Article CID Number.

ISSN: 0277-786X
ISSN: 1996-786X (electronic)

ISBN: 9781510602397
ISBN: 9781510602403 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA
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